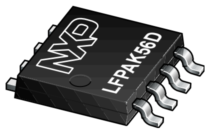


BUK9K17-60E

Dual N-channel 60 V, 17 mΩ logic level MOSFET

19 March 2014 Product data sheet

1. General description

Dual logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with $V_{GS(th)}$ rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

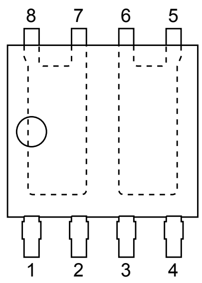
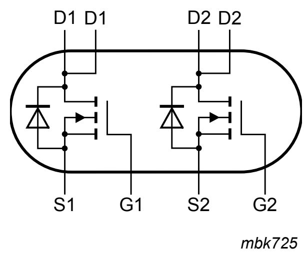
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j ≥ 25 °C; T_j ≤ 175 °C		-	-	60	V
I_D	drain current	V_{GS} = 5 V; T_{mb} = 25 °C; Fig. 2	[1]	-	-	26	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	-	53	W
Static characteristics FET1 and FET2							
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 10 A; T_j = 25 °C; Fig. 11		-	14	17	mΩ
Dynamic characteristics FET1 and FET2							
Q_{GD}	gate-drain charge	I_D = 10 A; V_{DS} = 48 V; V_{GS} = 5 V; T_j = 25 °C; Fig. 13; Fig. 14		-	5.7	-	nC

[1] Continuous current is limited by package.

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	 **LFPAK56D (SOT1205)**	
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		
7	D1	drain1		
8	D1	drain1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9K17-60E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9K17-60E	91760E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j ≥ 25 °C; T_j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ		-	60	V
V_{GS}	gate-source voltage	T_j ≤ 175 °C; DC		-10	10	V
		T_j ≤ 175 °C; Pulsed	[1][2]	-15	15	V
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	53	W
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 5 V; Fig. 2	[3]	-	26	A
		T_{mb} = 100 °C; V_{GS} = 5 V; Fig. 2		-	26	A

Symbol	Parameter	Conditions		Min	Max	Unit
I_{DM}	peak drain current	T_{mb} = 25 °C; pulsed; t_p ≤ 10 µs; Fig. 3		-	148	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode FET1 and FET2						
I_S	source current	T_{mb} = 25 °C	[3]	-	26	A
I_{SM}	peak source current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C		-	148	A
Avalanche Ruggedness FET1 and FET2						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 26 A; V_{sup} ≤ 60 V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; Fig. 4	[4][5]	-	64	mJ

[1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
[2] Significantly longer life times are achieved by lowering T_j and or V_{GS}.
[3] Continuous current is limited by package.
[4] Refer to application note AN10273 for further information
[5] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

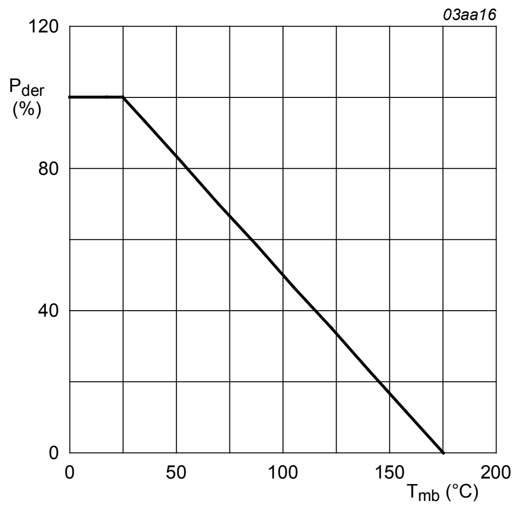


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

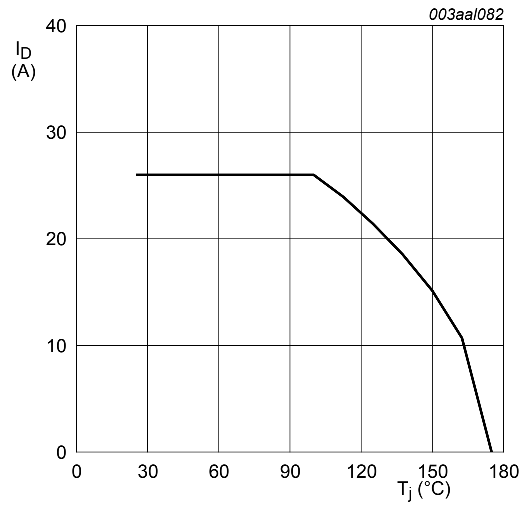


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 5V$$

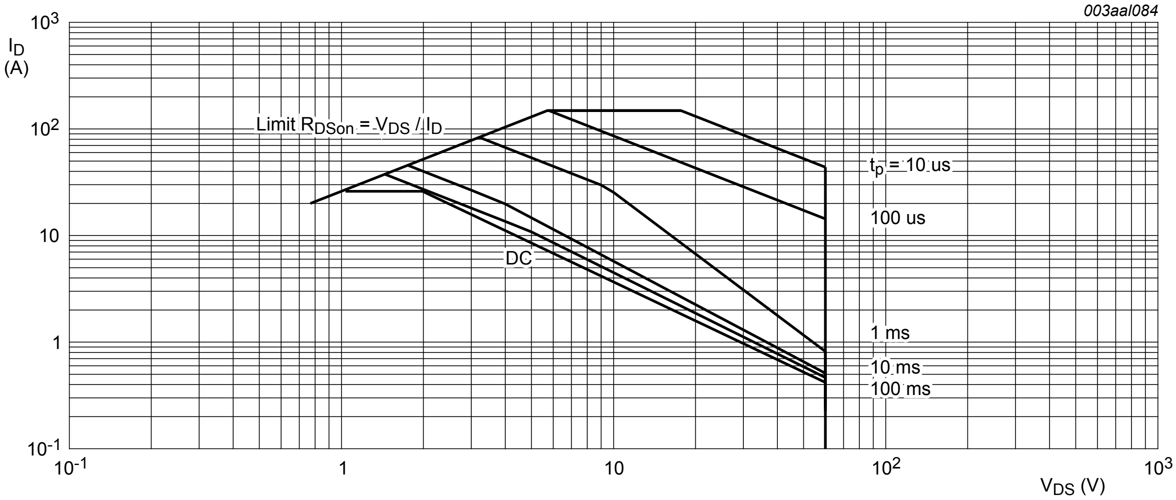


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25°C;\ I_{DM}$ is a single pulse

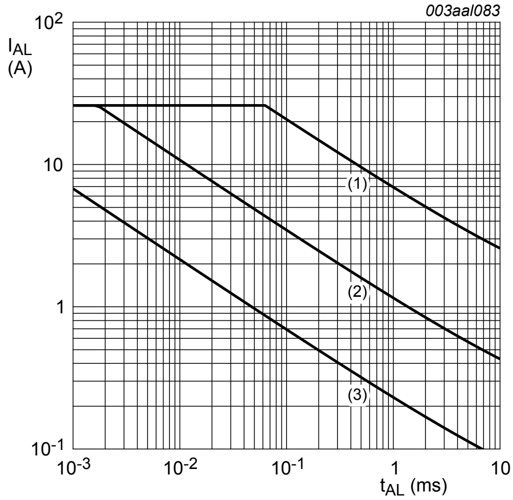


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j\ (init)} = 25°C$; (2) $T_{j\ (init)} = 150°C$; (3) Repetitive Avalanche

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	-	2.84	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board		-	95	-	K/W

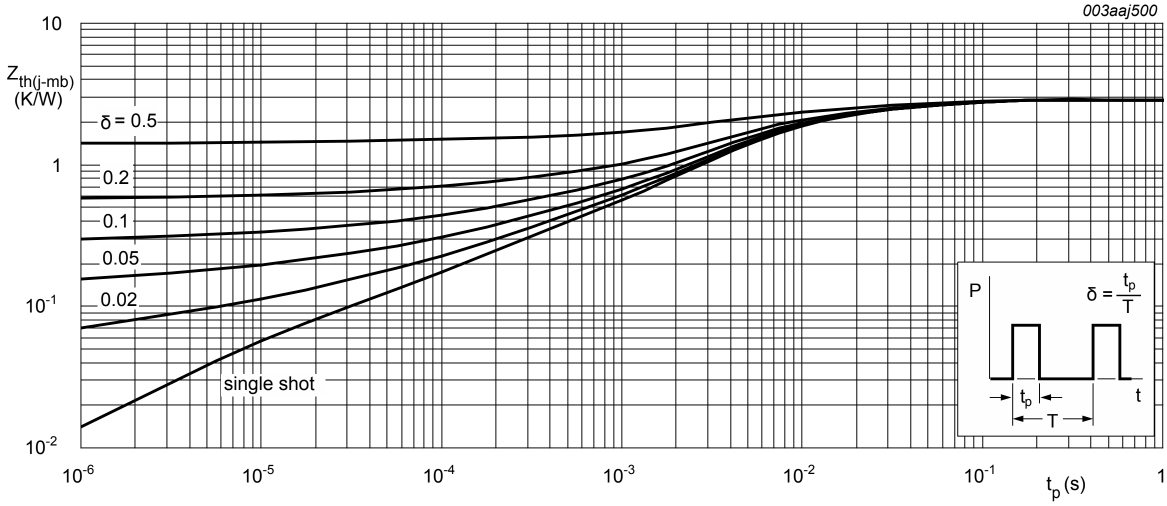


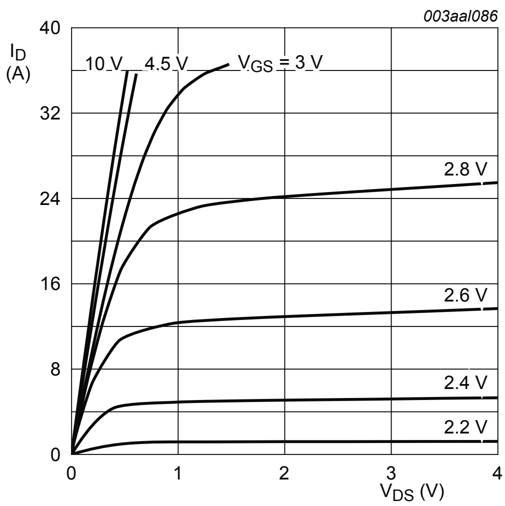
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration.

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics FET1 and FET2							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		54	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 9; Fig. 10		1.4	1.7	2.1	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 9; Fig. 10		0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 9; Fig. 10		-	-	2.45	V
I_{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C		-	0.02	1	µA
		V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 10 A; T_j = 25 °C; Fig. 11		-	14	17	mΩ
		V_{GS} = 5 V; I_D = 10 A; T_j = 175 °C; Fig. 11; Fig. 12		-	31.6	38.4	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; Fig. 11		-	12.4	15.6	mΩ
Dynamic characteristics FET1 and FET2							
$Q_{G(tot)}$	total gate charge	I_D = 10 A; V_{DS} = 48 V; V_{GS} = 5 V; T_j = 25 °C; Fig. 13; Fig. 14		-	16.5	-	nC
Q_{GS}	gate-source charge			-	3.3	-	nC

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Q_{GD}	gate-drain charge			-	5.7	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	1667	2223	pF
C_{oss}	output capacitance			-	160	193	pF
C_{rss}	reverse transfer capacitance	V_{GS} = 0 V; V_{DS} = 48 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	91	124	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 48 V; R_L = 5 Ω; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω; T_j = 25 °C; I_D = 10 A		-	10.7	-	ns
t_r	rise time			-	20	-	ns
$t_{d(off)}$	turn-off delay time			-	23	-	ns
t_f	fall time			-	19.2	-	ns
Source-drain diode FET1 and FET2							
V_{SD}	source-drain voltage	I_S = 10 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 16		-	0.78	1.2	V
t_{rr}	reverse recovery time	I_S = 10 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 30 V; T_j = 25 °C		-	20.3	-	ns
Q_r	recovered charge			-	16.7	-	nC



T_j = 25 °C; t_p = 300 µs

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

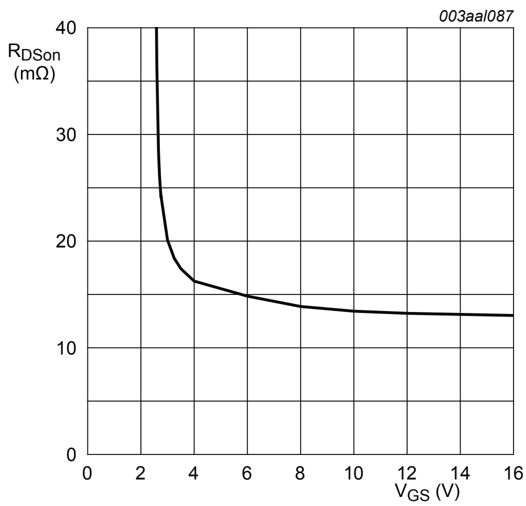


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25°C;\ I_D = 10A$

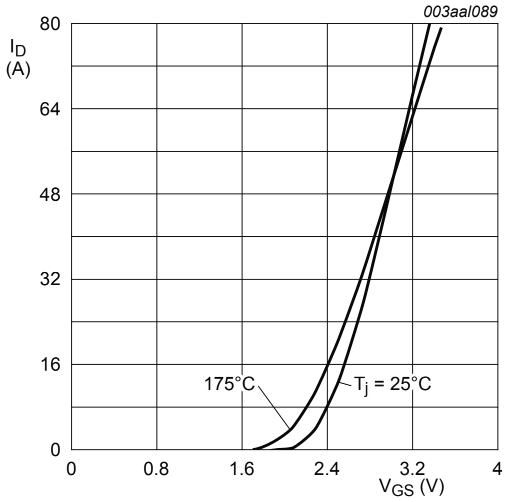


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

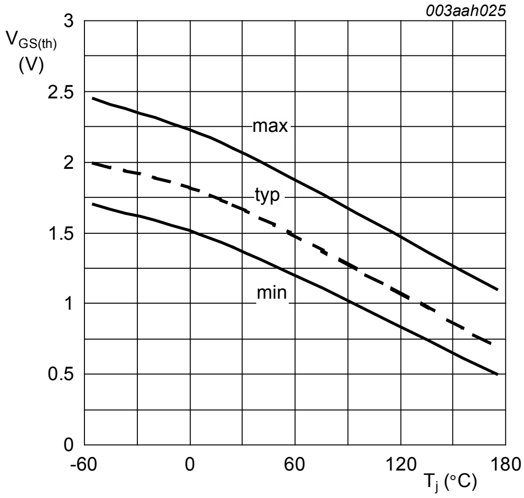


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1$ mA; $V_{DS} = V_{GS}$

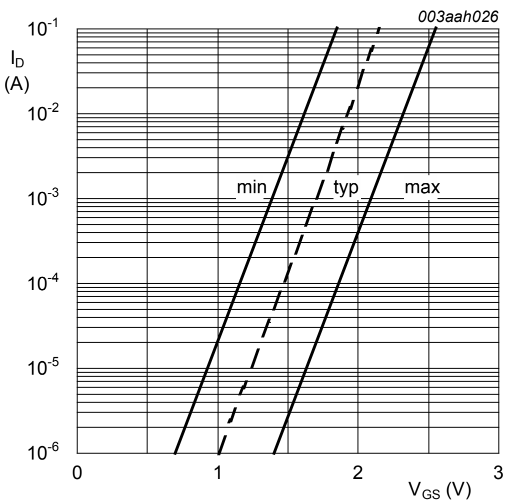
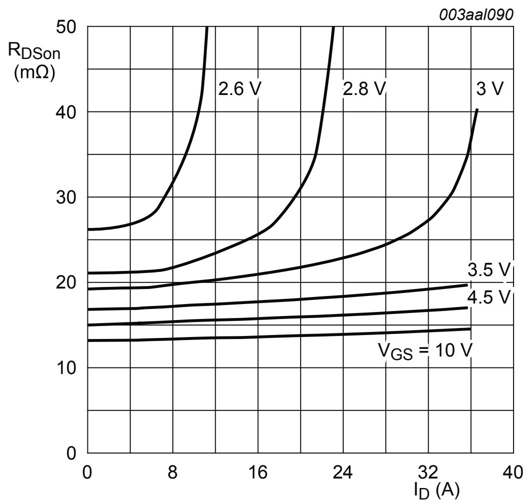


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25°C$; $V_{DS} = 5V$



T_j = 25 °C; t_p = 300 μs

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

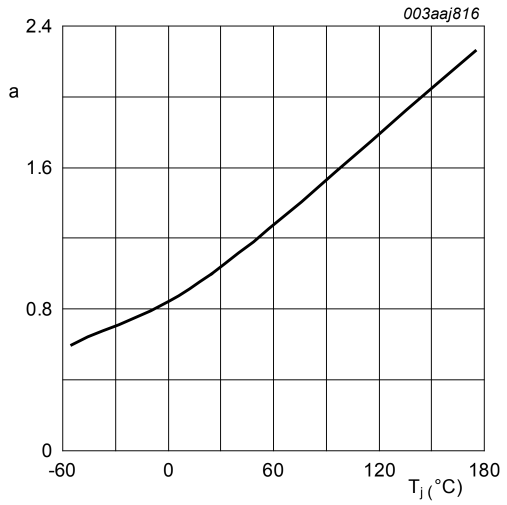


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon\,(25°C)}}$$

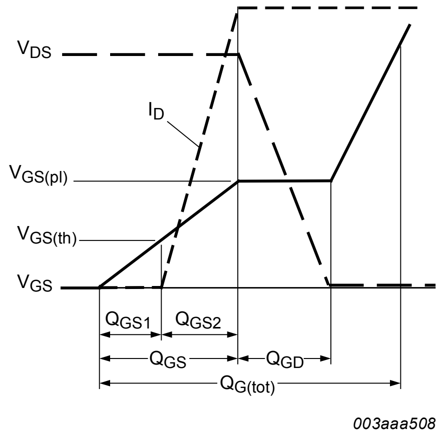


Fig. 13. Gate charge waveform definitions

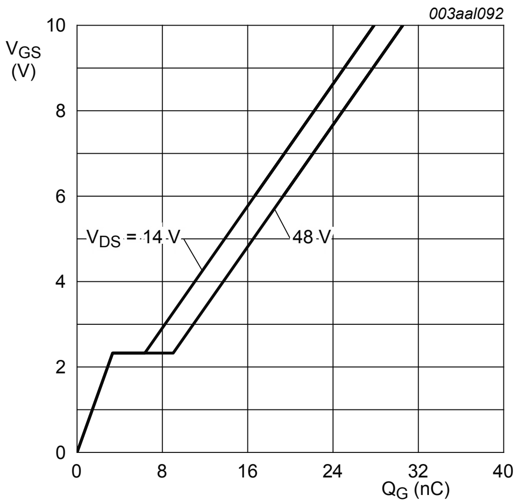


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$T_j = 25°C;\ I_D = 10A$

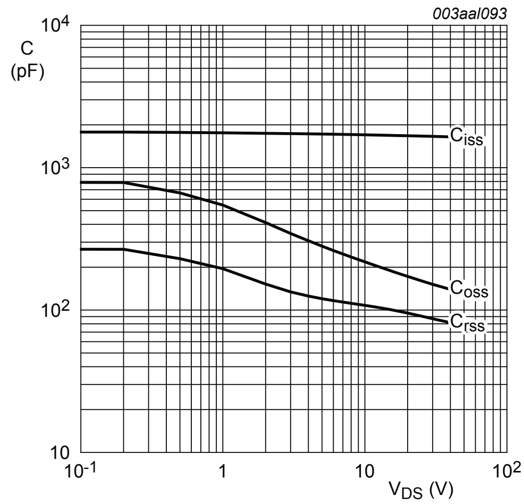


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V;\ f = 1MHz$

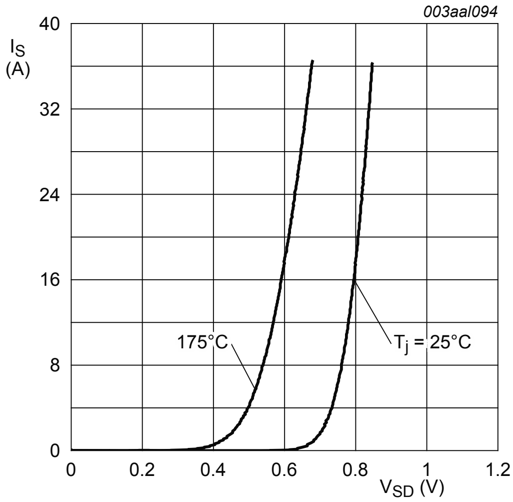
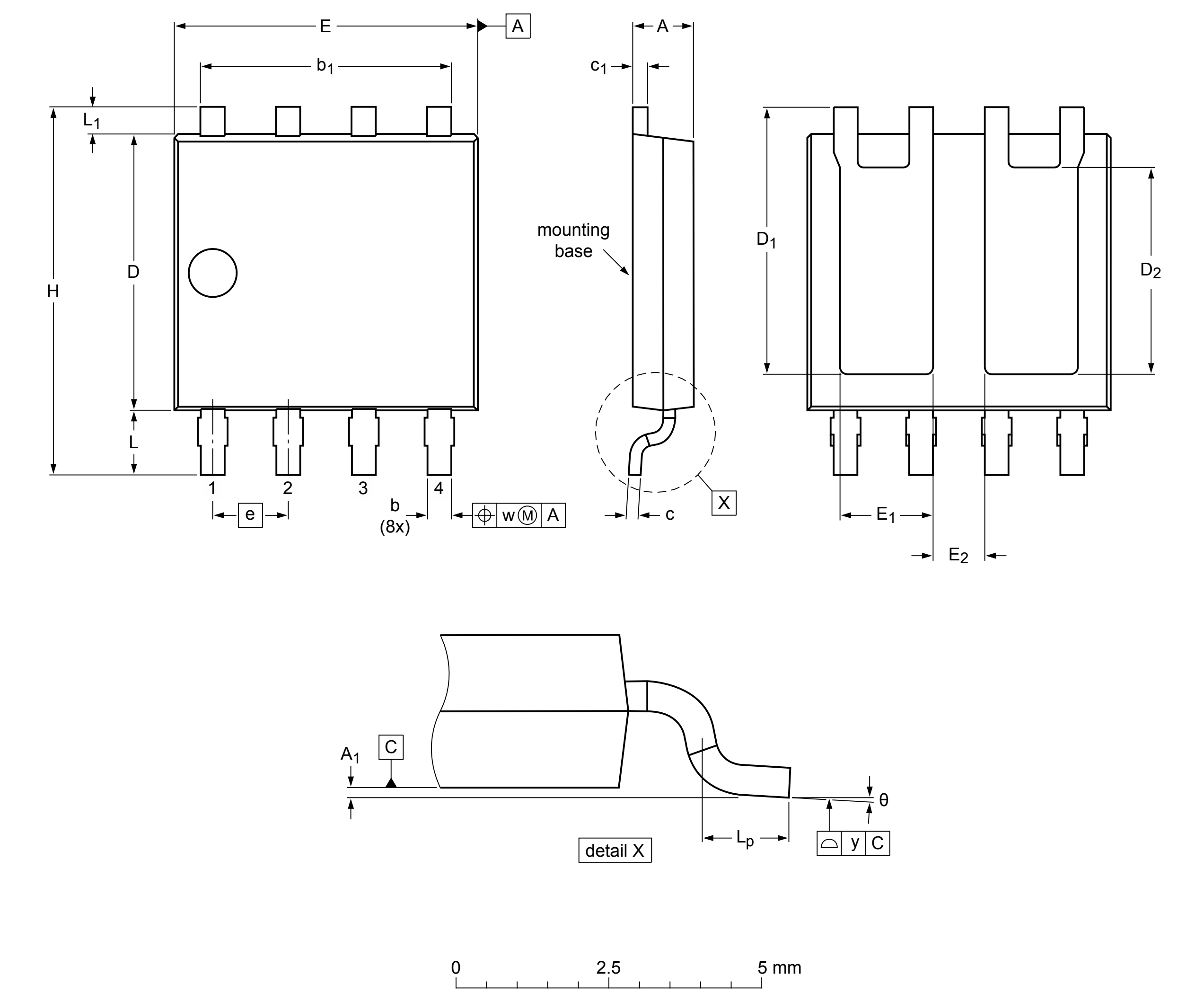


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0V$

11. Package outline

Plastic single ended surface mounted package (LFPAK56D); 8 leads **SOT1205**



Dimensions

Unit		A	A_1	b	b_1	c	c_1	$D^{(1)}$	$D_1^{(1)}$	D_2 (ref)	$E^{(1)}$	$E_1^{(1)}$	E_2	e	H	L	L_1	L_p	w	y	θ
mm	max	1.05	0.1	0.50	4.4	0.25	0.30	4.70	4.8		5.30	1.8	0.85		6.2	1.3	0.55	0.85			8°
	nom									3.5				1.27					0.25	0.1	
	min		0.0	0.35	4.1	0.19	0.24	4.45			4.95	1.6			5.9	0.8	0.30	0.40			0°

Note
1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

sot1205_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1205						~~13-02-19~~ 13-02-21

Fig. 17. Package outline LFPAK56D (SOT1205)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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